

## N-Channel 40-V (D-S) MOSFET

| <b>PRODUCT SUMMARY</b> |                           |                        |              |
|------------------------|---------------------------|------------------------|--------------|
| $V_{DS}$ (V)           | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) <sup>f</sup> | $Q_g$ (Typ.) |
| 40                     | 0.0075 at $V_{GS} = 10$ V | 58                     | 21 nC        |
|                        | 0.009 at $V_{GS} = 4.5$ V | 53                     |              |

### FEATURES

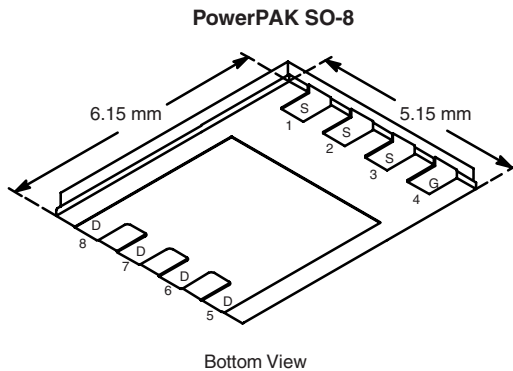
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  and UIS Tested



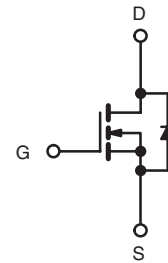
**RoHS**  
COMPLIANT

### APPLICATIONS

- Synchronous Rectifier



Ordering Information: Si7884BDP-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

| <b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25$ °C, unless otherwise noted |                |               |                      |   |
|---|----------------|---------------|----------------------|---|
| Parameter   | Symbol         | Limit         | Unit                 |   |
| Drain-Source Voltage  | $V_{DS}$       | 40            | V                    |   |
| Gate-Source Voltage   | $V_{GS}$       | $\pm 20$      |                      |   |
| Continuous Drain Current ( $T_J = 150$ °C)                            | $I_D$          | $T_C = 25$ °C | 58 <sup>f</sup>      | A |
|   |                | $T_C = 70$ °C | 46 <sup>f</sup>      |   |
|   |                | $T_A = 25$ °C | 18.5 <sup>a, b</sup> |   |
|   |                | $T_A = 70$ °C | 14.8 <sup>a, b</sup> |   |
| Pulsed Drain Current  | $I_{DM}$       | 50            |                      |   |
| Avalanche Current   | $I_{AS}$       | 33            | mJ                   |   |
| Avalanche Energy  |                |               |                      |   |
| Continuous Source-Drain Diode Current                                 | $I_S$          | $T_C = 25$ °C | 38 <sup>f</sup>      | A |
|   |                | $T_A = 25$ °C | 3.8 <sup>a, b</sup>  |   |
| Maximum Power Dissipation   | $P_D$          | $T_C = 25$ °C | 46                   | W |
|   |                | $T_C = 70$ °C | 29                   |   |
|   |                | $T_A = 25$ °C | 4.6 <sup>a, b</sup>  |   |
|   |                | $T_A = 70$ °C | 3.0 <sup>a, b</sup>  |   |
| Operating Junction and Storage Temperature Range                      | $T_J, T_{stg}$ | - 55 to 150   | °C                   |   |
| Soldering Recommendations (Peak Temperature) <sup>c, d</sup>          |                | 260           |                      |   |

| <b>THERMAL RESISTANCE RATINGS</b>           |            |         |         |      |  |
|---|------------|---------|---------|------|--|
| Parameter                                   | Symbol     | Typical | Maximum | Unit |  |
| Maximum Junction-to-Ambient <sup>a, e</sup> | $R_{thJA}$ | 22      | 27      | °C/W |  |
| Maximum Junction-to-Case (Drain)            | $R_{thJC}$ | 2.2     | 2.7     |      |  |

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 70 °C/W.
- Calculation based on maximum allowable junction temperature. Package limitation current is 32 A.

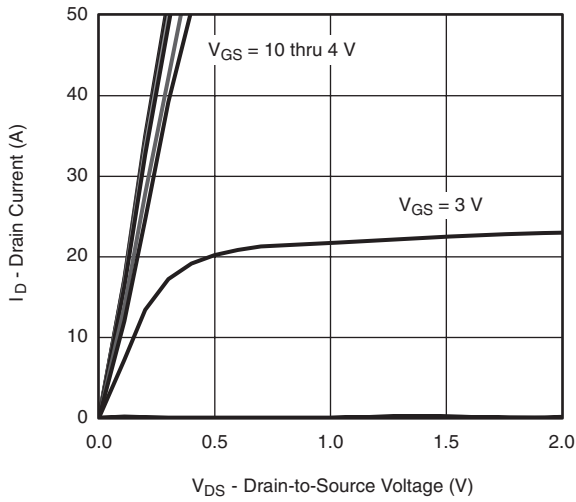
| <b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted |                         |   |      |        |           |               |
|---|-------------------------|---|------|--------|-----------|---------------|
| Parameter   | Symbol                  | Test Conditions   | Min. | Typ.   | Max.      | Unit          |
| <b>Static</b>   |                         |   |      |        |           |               |
| Drain-Source Breakdown Voltage  | $V_{DS}$                | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$   | 40   |        |           | V             |
| $V_{DS}$ Temperature Coefficient  | $\Delta V_{DS}/T_J$     | $I_D = 250\text{ }\mu\text{A}$  |      | 46     |           | mV/°C         |
| $V_{GS(th)}$ Temperature Coefficient  | $\Delta V_{GS(th)}/T_J$ |   |      | -6.7   |           |               |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$            | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$   | 1    |        | 3         | V             |
| Gate-Source Leakage   | $I_{GSS}$               | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$   |      |        | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current   | $I_{DSS}$               | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$   |      |        | 1         | $\mu\text{A}$ |
|   |                         | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$   |      |        | 5         |               |
| On-State Drain Current <sup>a</sup>   | $I_{D(on)}$             | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$  | 50   |        |           | A             |
| Drain-Source On-State Resistance <sup>a</sup>                                   | $R_{DS(on)}$            | $V_{GS} = 10\text{ V}, I_D = 16\text{ A}$   |      | 0.0062 | 0.0075    | $\Omega$      |
|   |                         | $V_{GS} = 4.5\text{ V}, I_D = 14\text{ A}$  |      | 0.0073 | 0.009     |               |
| Forward Transconductance <sup>a</sup>   | $g_{fs}$                | $V_{DS} = 15\text{ V}, I_D = 16\text{ A}$   |      | 55     |           | S             |
| <b>Dynamic<sup>b</sup></b>  |                         |   |      |        |           |               |
| Input Capacitance   | $C_{iss}$               | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$   |      | 3540   |           | pF            |
| Output Capacitance  | $C_{oss}$               |   |      | 335    |           |               |
| Reverse Transfer Capacitance  | $C_{rss}$               |   |      | 142    |           |               |
| Total Gate Charge   | $Q_g$                   | $V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 16\text{ A}$   |      | 51     | 77        | nC            |
|   |                         | $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 16\text{ A}$  |      | 21     | 32        |               |
| Gate-Source Charge  | $Q_{gs}$                |   |      | 10.7   |           |               |
| Gate-Drain Charge   | $Q_{gd}$                |   | 3.0  |        |           |               |
| Gate Resistance   | $R_g$                   | $f = 1\text{ MHz}$  |      | 0.75   | 1.5       | $\Omega$      |
| Turn-On Delay Time  | $t_{d(on)}$             | $V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$<br>$I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$ |      | 30     | 45        | ns            |
| Rise Time   | $t_r$                   |   |      | 14     | 21        |               |
| Turn-Off Delay Time   | $t_{d(off)}$            |   |      | 38     | 60        |               |
| Fall Time   | $t_f$                   |   |      | 11     | 17        |               |
| Turn-On Delay Time  | $t_{d(on)}$             | $V_{DD} = 20\text{ V}, R_L = 2\text{ }\Omega$<br>$I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$  |      | 14     | 21        |               |
| Rise Time   | $t_r$                   |   |      | 10     | 15        |               |
| Turn-Off Delay Time   | $t_{d(off)}$            |   |      | 32     | 50        |               |
| Fall Time   | $t_f$                   |   |      | 8      | 15        |               |
| <b>Drain-Source Body Diode Characteristics</b>                                  |                         |   |      |        |           |               |
| Continuous Source-Drain Diode Current   | $I_S$                   | $T_C = 25\text{ }^\circ\text{C}$  |      |        | 32        | A             |
| Pulse Diode Forward Current   | $I_{SM}$                |   |      |        | 50        |               |
| Body Diode Voltage  | $V_{SD}$                | $I_S = 10\text{ A}, V_{GS} = 0\text{ V}$  |      | 0.8    | 1.2       | V             |
| Body Diode Reverse Recovery Time  | $t_{rr}$                | $I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$                                   |      | 25     | 50        | ns            |
| Body Diode Reverse Recovery Charge  | $Q_{rr}$                |   |      | 19     | 38        | nC            |
| Reverse Recovery Fall Time  | $t_a$                   |   |      | 13     |           | ns            |
| Reverse Recovery Rise Time  | $t_b$                   |   |      | 12     |           |               |

## Notes:

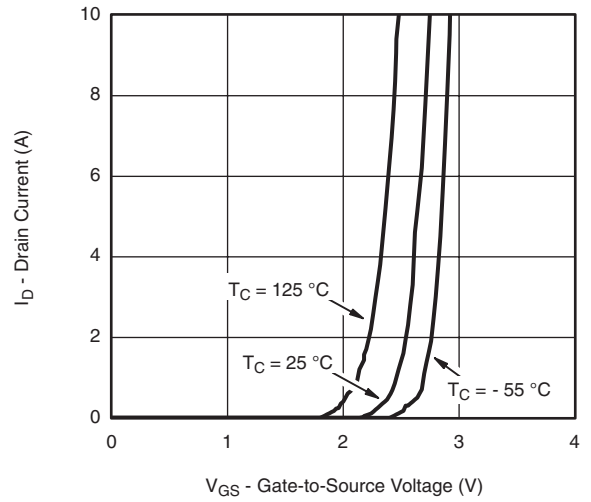
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

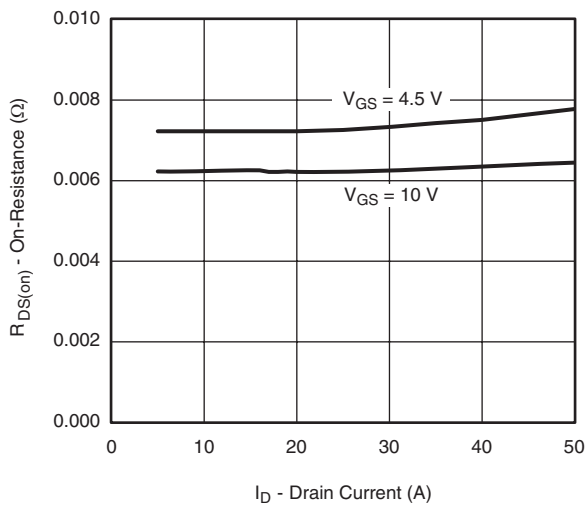
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



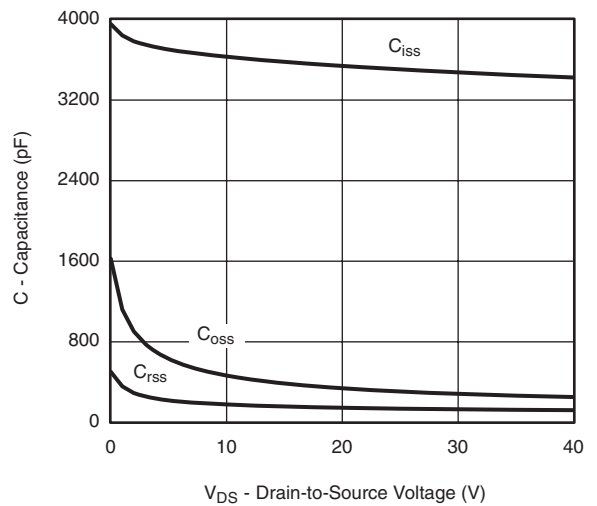
**Output Characteristics**



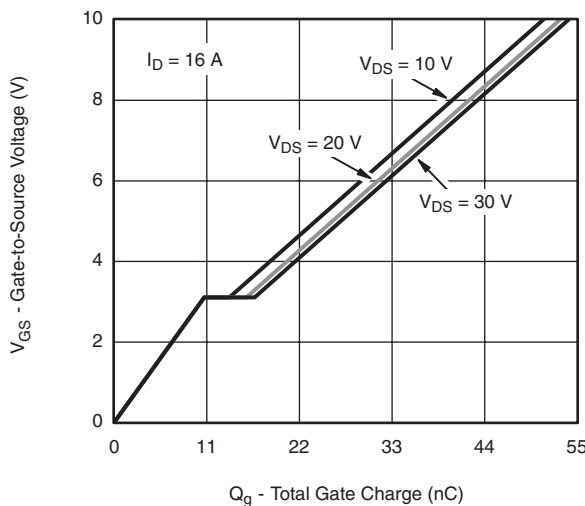
**Transfer Characteristics**



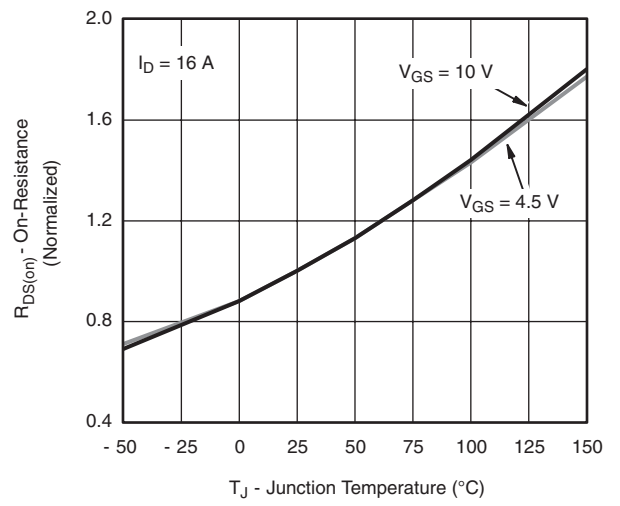
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

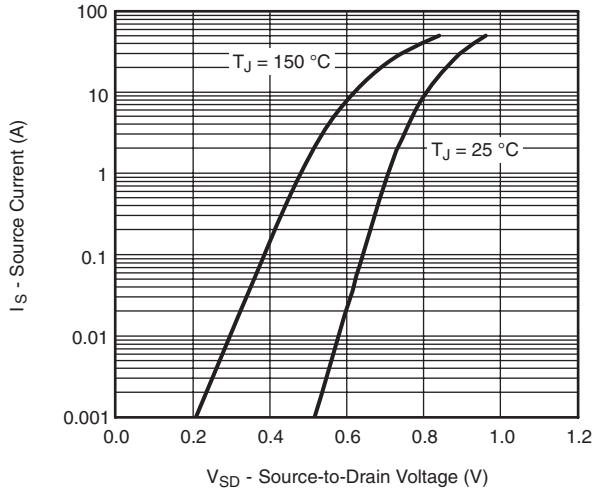


**Gate Charge**

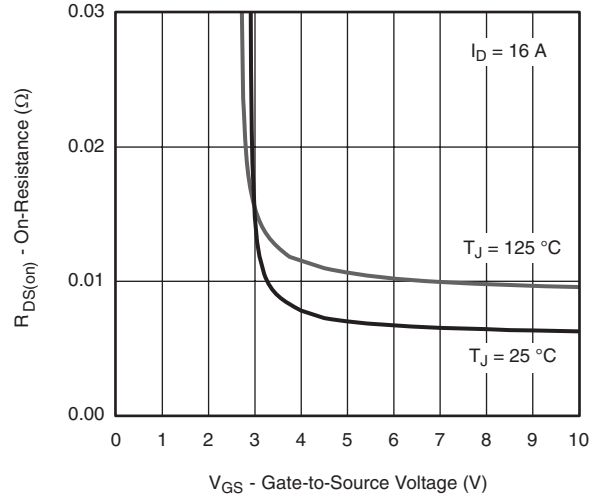


**On-Resistance vs. Junction Temperature**

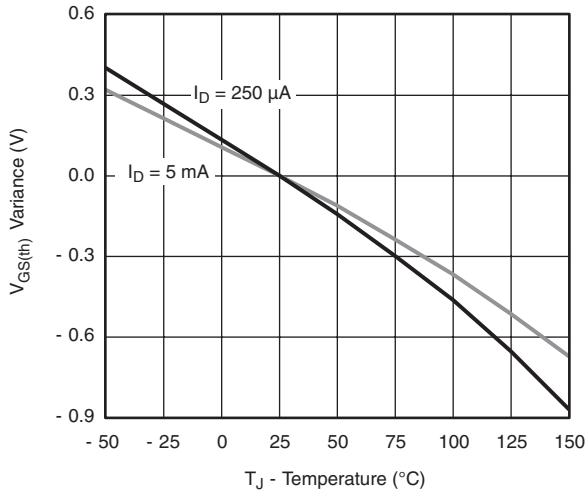
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



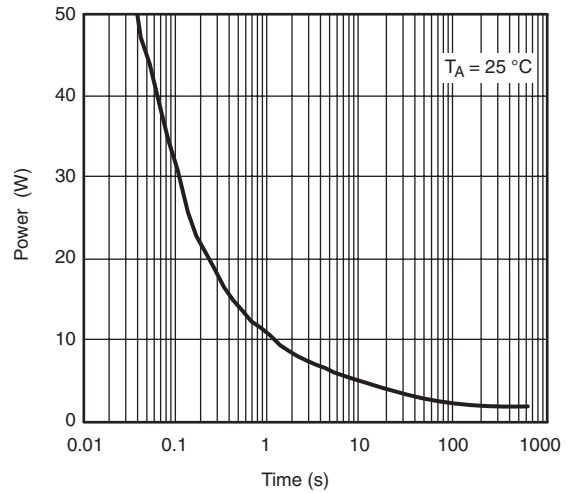
Source-Drain Diode Forward Voltage



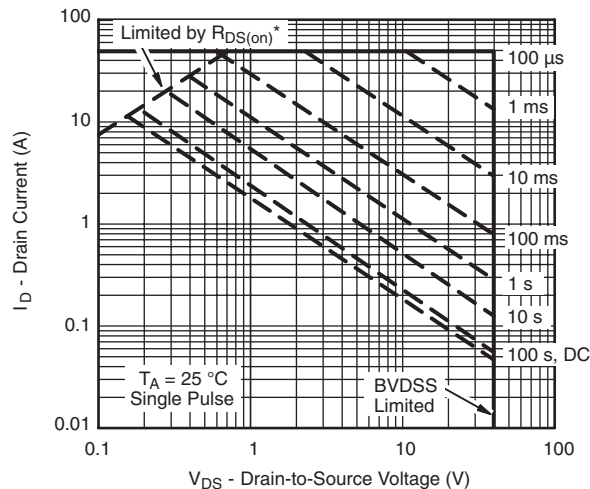
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



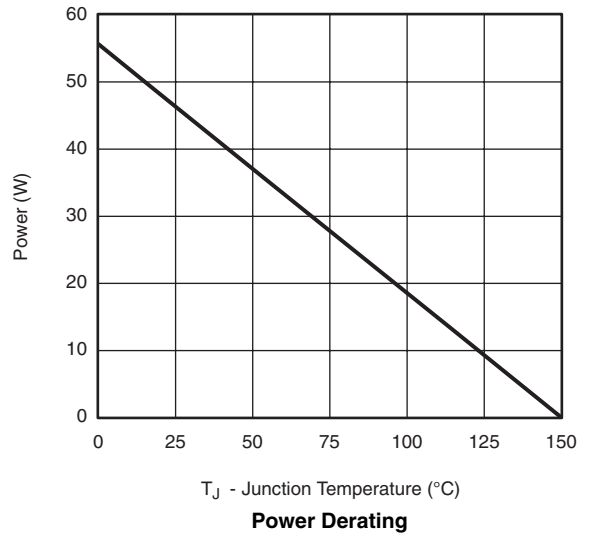
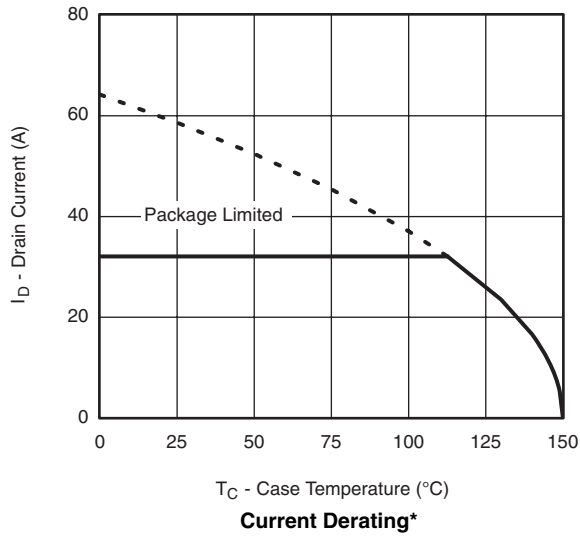
Single Pulse Power (Junction-to-Ambient)



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

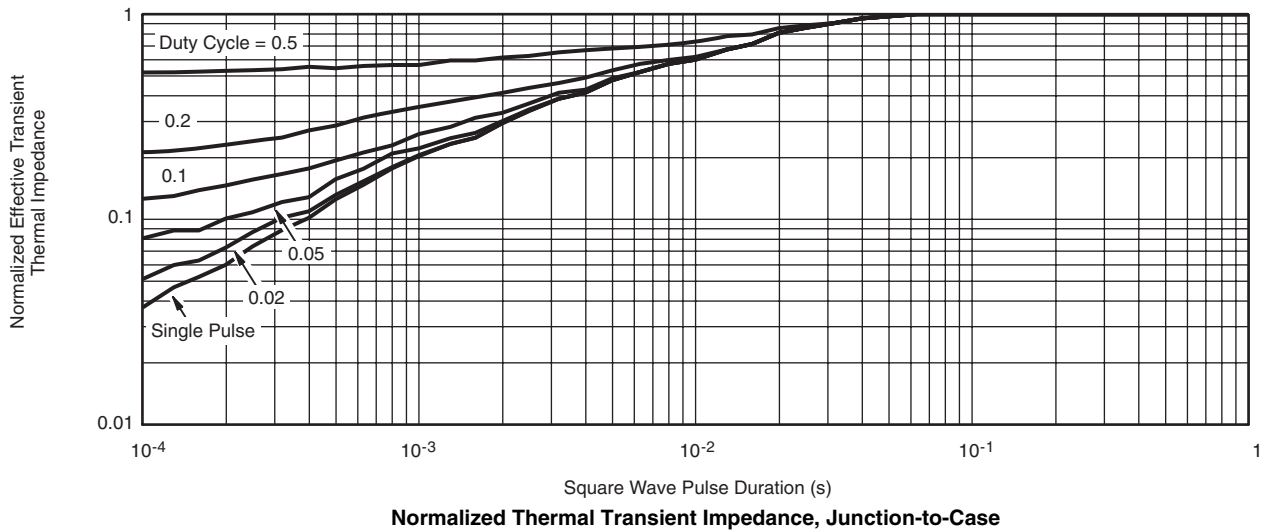
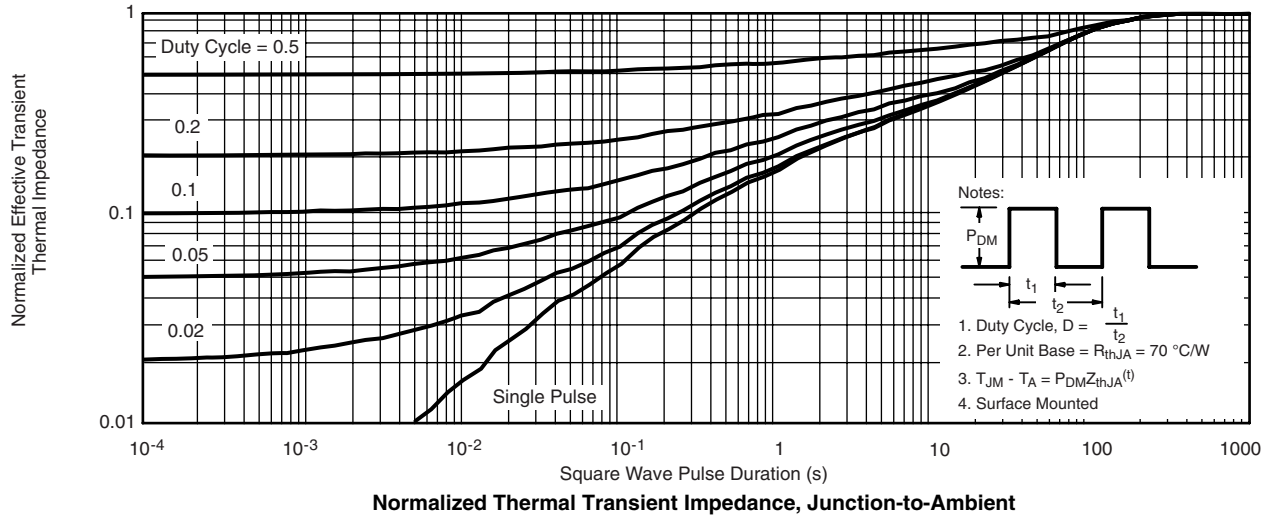
Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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